N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

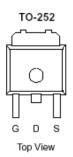
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vos (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
150	69 @ V _{GS} = 10V	22		
150	110 @ V _{GS} = 5.5V	18		

in l





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			150	V	
Gate-Source Voltage			±20	v	
Continuous Drain Current ^a	T _C =25°C	I _D	22	А	
Pulsed Drain Current ^b			60	~	
Continuous Source Current (Diode Conduction) ^a			51	А	
Power Dissipation ^a	T _C =25°C	PD	50	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{ extsf{ heta}JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	0/11		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 120 V, V_{GS} = 0 V$			1 uA		
Zero Gale Voltage Drain Guirent	DSS	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	40			А	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$			69	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, \text{ I}_{D} = 8 \text{ A}$			110	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		38		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 25.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V	
		Dynamic ^b					
Total Gate Charge	Qg			24			
Gate-Source Charge	Q _{gs}	$V_{DS} = 75 \text{ V}, \text{ V}_{GS} = 5.5 \text{ V},$ $I_{D} = 10 \text{ A}$		7.8		nC	
Gate-Drain Charge	Q_gd	1 <u>0</u> – 10 A		9.7			
Turn-On Delay Time	t _{d(on)}			13			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, \text{ R}_{L} = 7.5 \Omega, \text{ I}_{D} = 10 \text{ A},$		22		200	
Turn-Off Delay Time	t _{d(off)}	V_{GEN} = 10 V, R_{GEN} = 6 Ω		64		ns	
Fall Time	t _f	<u> </u>		36			
Input Capacitance	C _{iss}			2599			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		167		pF	
Reverse Transfer Capacitance	C _{rss}]		90			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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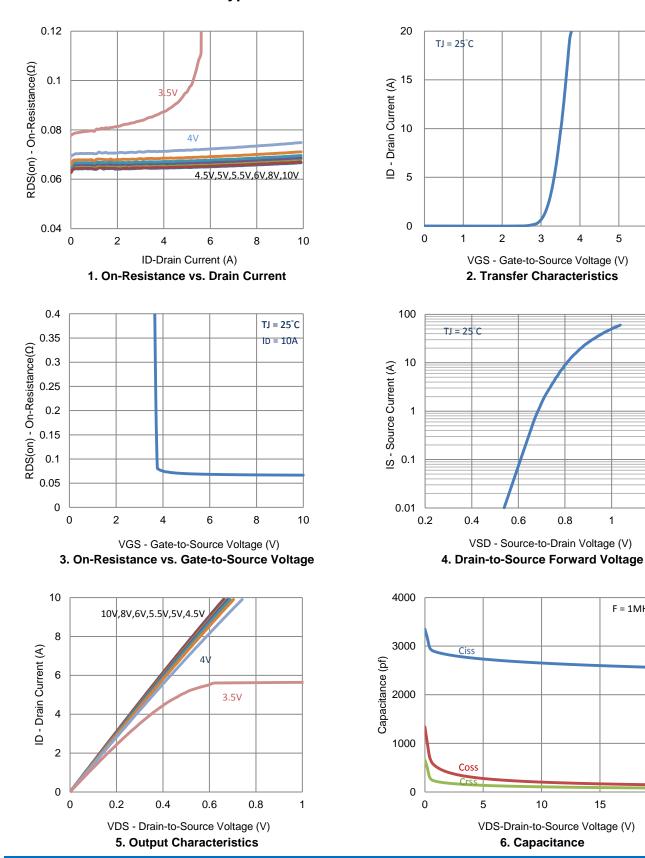
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F = 1MHz

1.2

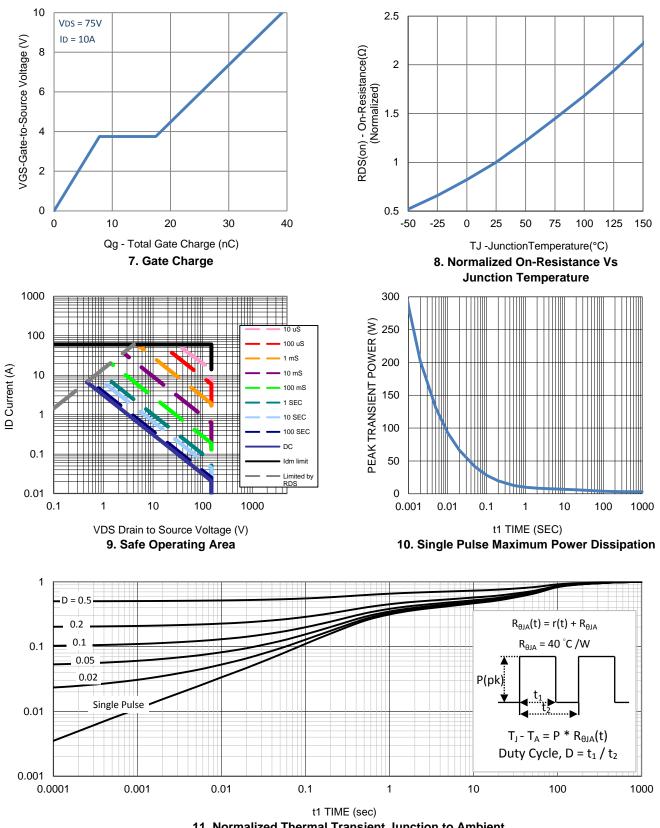
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Typical Electrical Characteristics

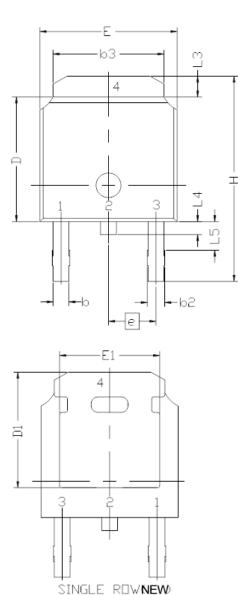
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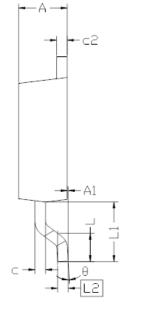


Typical Electrical Characteristics

11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENIO		DEONTO
SYMBOL	DIMENS: MIN	IUNAL I NOM	KEUMIS I MAX
F	6.40	6,60	6.731
	1.40	1.52	1.77
			EF
L2	0.	508 BS	C
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6.223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2,	286 BS	SC .
A	2.20	2.30	2.38
A1	0		0.127
\subset	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5,30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.